## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

1	1. (Currently amended) A microrelay, comprising:
2	a first signal line;
3	a second signal line;
4	a contact head configured to make an electrical connection between the
5	first signal line and the second signal line; and
6	an electro-thermal actuator coupled to the contact head and configured to
7	laterally displace the contact head so that the closing action of the contact head is
8	parallel to the plane of a semiconductor wafer upon which the microrelay is
9	fabricated;
10	wherein the contact head and associated portions of the first and second
11	signal lines are covered with a layer of sputtered gold, and wherein a partial
12	release operation was performed at the closing gap to ensure the separation of
13	sputtered gold on the contact head sidewall and the signal lines.
1	2. (Original) The microrelay of claim 1,
2	wherein the electro-thermal actuator comprises a substantially V-shaped
3	beam;
4	wherein thermal expansion caused by current flowing through the
5	substantially V-shaped beam actuates the contact head to make the electrical
6	connection.

1	3. (Original) The microrelay of claim 1, wherein the electro-thermal
2	actuator comprises a substantially V-shaped central beam cascaded between two
3	substantially V-shaped side beams, which increase the displacement of the
4	substantially V-shaped central beam during actuation.
1	4. (Original) The microrelay of claim 1, wherein the electro-thermal
2	actuator is comprised of:
3	silicon;
4	polysilicon;
5	nickel; or
6	tungsten.
1	5 (Canceled).
1	6. (Original) The microrelay of claim 1, wherein the contact head is
2	coupled to the electro-thermal actuator through an insulator.
1	7. (Original) The microrelay of claim 6, wherein the insulator is comprised
2	of:
3	silicon nitride; or
4	silicon dioxide.
1	8 (Canceled).
1	9. (Currently amended) The microrelay of claim 1, wherein the shape of
	the contact head is:
2	
3	square;
4	<del>angled;</del> or

nded.

1	10. (Original) The microrelay of claim 1, wherein the microrelay is
2	fabricated using a process that involves:
3	deposition of low-stress silicon nitride as isolation;
4	deposition and patterning of sacrificial silicon dioxide;
5	deposition and patterning of a low-stress silicon nitride connection;
6	deposition and patterning of polysilicon;
7	a partial release operation;
8	sputtering and lift-off of gold; and
9	a full release operation.
1	11. (Original) The microrelay of claim 1, wherein the microrelay is an
2	element in an array of microrelays.
1	12. (Currently amended) A microrelay, comprising:
2	a first signal line;
3	a second signal line;
4	a contact head configured to make an electrical connection between the
5	first signal line and the second signal line; and
6	an electro-thermal actuator coupled to the contact head and configured to
7	laterally displace the contact head so that the closing action of the contact head is
8	parallel to the plane of a semiconductor wafer upon which the microrelay is
9	fabricated;
10	wherein the electro-thermal actuator comprises a substantially V-shaped
11	beam, wherein thermal expansion caused by current flowing through the
12	substantially V-shaped beam actuates the contact head to make the electrical
13	connection;

14	wherein the contact head and associated portions of the first and second
15	signal lines are covered with a layer of sputtered gold, and wherein a partial
16	release operation was performed at the closing gap to ensure the separation of
17	sputtered gold on the contact head sidewall and the signal lines.
1	13 (Canceled).
1	14. (Original) The microrelay of claim 12, wherein the contact head is
2	coupled to the electro-thermal actuator through an insulator.
1	15 (Canceled).
1	16. (Currently amended) The microrelay of claim 12, wherein the shape of
2	the contact head is:
3	square;
4	<del>angled;</del> or
5	rounded.
1	17-20 (Canceled).